

Description

The AR1521P0 is a bi-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The AR1521P0 has an ultra-low capacitance with a typical value at 0.3pF, and complies with the IEC 61000-4-2 (ESD) with $\pm 20\text{kV}$ air and $\pm 15\text{kV}$ contact discharge. It is assembled into an ultra-small 0.6x0.3x0.3mm lead-free DFN package. The small size, ultra-low capacitance and high ESD surge protection make AR1521P0 an ideal choice to protect cell phone and high-power USB.

Features

- Ultra low capacitance: 0.3pF typical
- Ultra low leakage: nA level
- Operating voltage: 15V
- Low clamping voltage
- 2-pin leadless package
- Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
Air discharge: $\pm 20\text{kV}$
Contact discharge: $\pm 15\text{kV}$
 - IEC61000-4-5 (Lightning) 2.5A (8/20 μs)
- RoHS Compliant

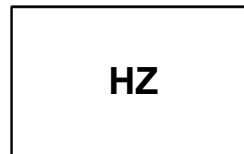
Mechanical Characteristics

- Package: DFN0603-2
- Case Material: “Green” Molding Compound.
- Terminal Connections: See Diagram Below
- Marking Information: See Below

Applications

- Cellular Handsets and Accessories
- Serial ATA
- MDDI Ports
- USB Ports
- PCI Express and Serial SATA Ports

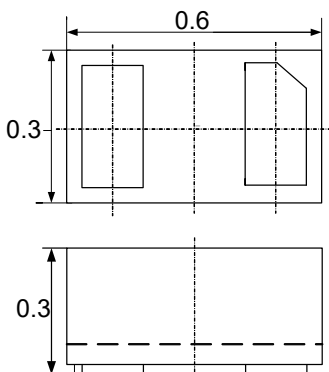
Marking Information



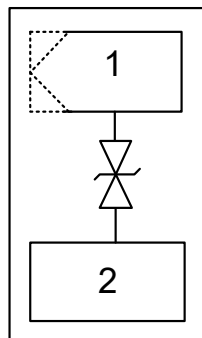
Ordering Information

Part Number	Packaging	Reel Size
AR1521P0	10000/Tape & Reel	7 inch

Dimensions and Pin Configuration



Package Dimensions



Circuit and Pin Schematic

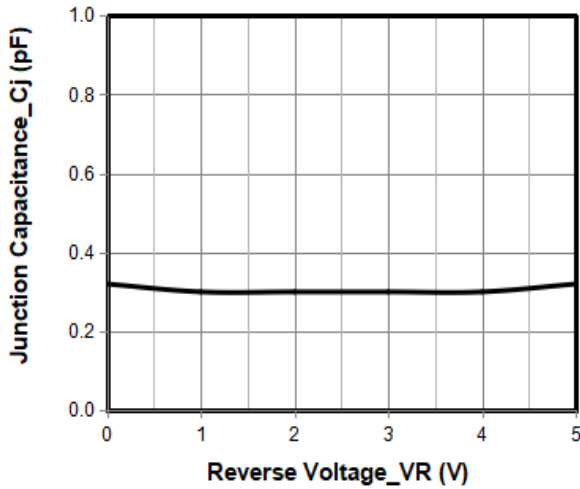
Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	Ppk	90	W
Peak Pulse Current (8/20μs)	I _{PP}	2.5	A
ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact)	V _{ESD}	±20 ±15	kV
Operating Temperature Range	T _J	-55 to +125	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C

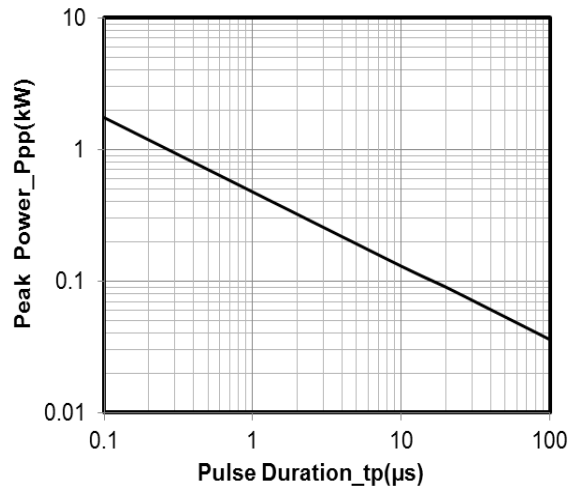
Electrical Characteristics (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V _{RWM}			15	V	
Breakdown Voltage	V _{BR}	16.7			V	I _T = 1mA
Reverse Leakage Current	I _R			0.2	μA	V _{RWM} = 15V
Clamping Voltage	V _C			26	V	I _{PP} = 1A (8 x 20μs pulse)
Clamping Voltage	V _C			35	V	I _{PP} = 2.5A (8 x 20μs pulse)
Junction Capacitance	C _J		0.3	0.5	pF	V _R = 0V, f = 1MHz

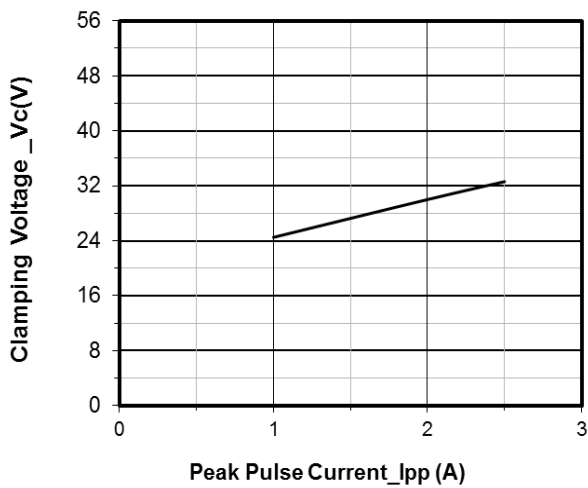
Typical Performance Characteristics (TA=25°C unless otherwise Specified)



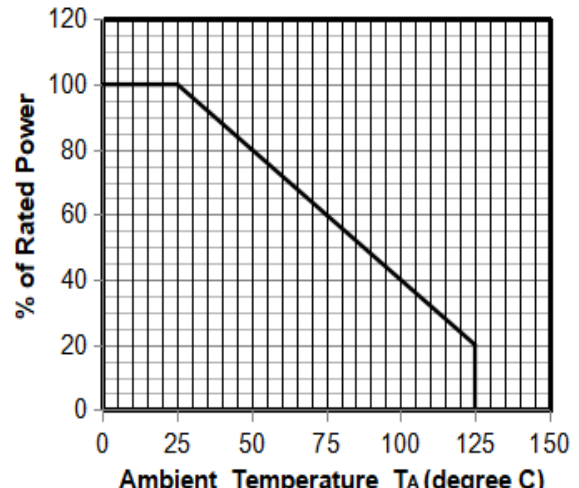
Junction Capacitance vs. Reverse Voltage



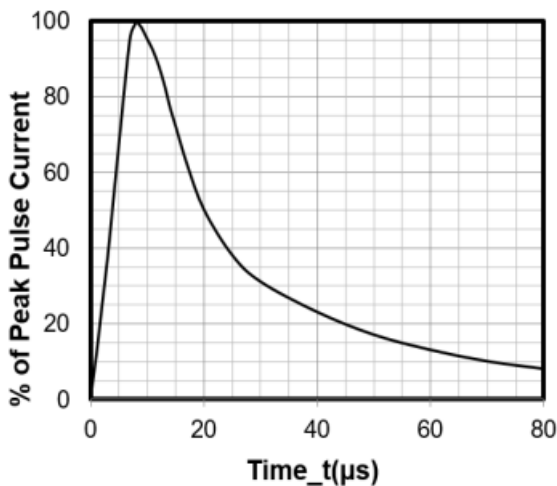
Peak Pulse Power vs. Pulse Time



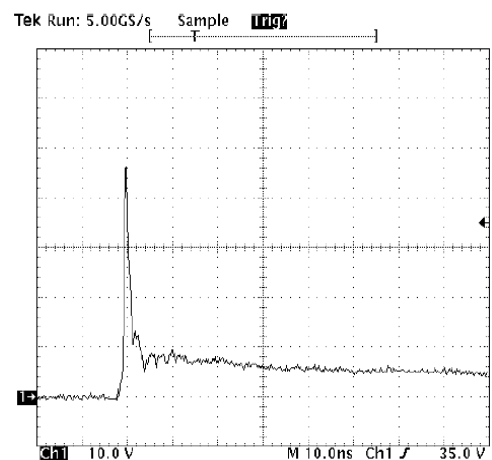
Clamping Voltage vs. Peak Pulse Current



Power Derating Curve



8 X 20μs Pulse Waveform

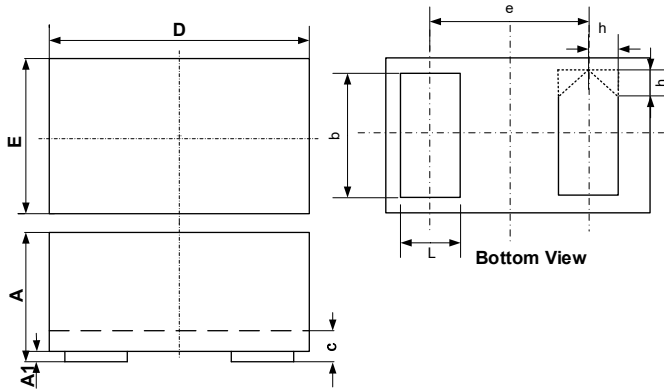


Note: Data is taken with a 10x attenuator

ESD Clamping Voltage

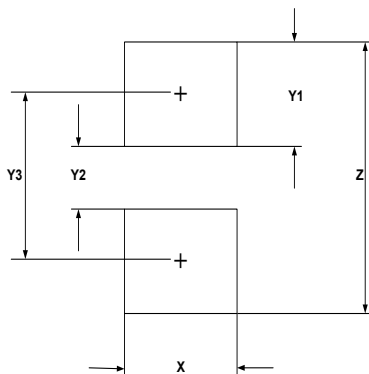
8 kV Contact per IEC61000-4-2

DFN0603-2 Package Outline Drawing



SYM	DIMENSIONS		
	MILLIMETERS		
	MIN	NOM	MAX
A	0.230		0.330
A1	0.000	0.020	0.050
b	0.215	0.245	0.275
c	0.120	0.150	0.180
D	0.550	0.600	0.650
e	0.355 BSC		
E	0.250	0.300	0.350
L	0.160	0.190	0.220
h	0.079 BSC		

Suggested Land Pattern



SYM	DIMENSIONS	
	MILLIMETERS	INCHES
X	0.30	0.012
Y1	0.25	0.010
Y2	0.15	0.006
Y3	0.40	0.016
Z	0.65	0.026

Contact Information

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